



5NM70-U2

Power MOSFET

5.4A, 700V N-CHANNEL SUPER-JUNCTION MOSFET

DESCRIPTION

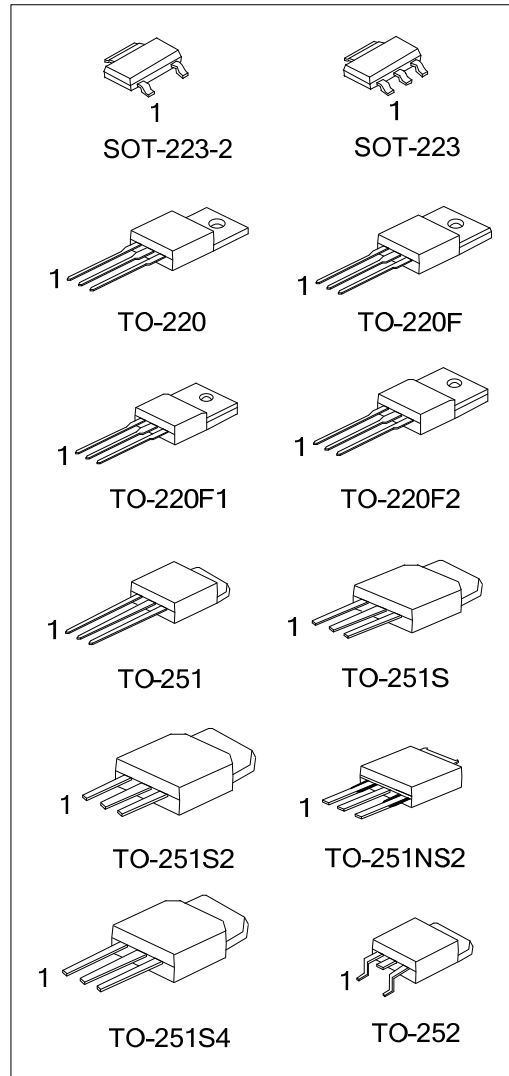
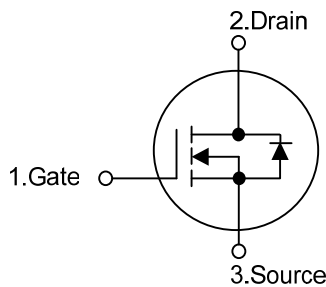
The UTC **5NM70-U2** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics.

This power MOSFET is usually used in high speed switching applications at power supplies, PWM motor controls, high efficient AC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} \leq 1.5 \Omega @ V_{GS} = 10V, I_D = 2.5A$
- * Fast Switching Capability
- * Improved dv/dt Capability, High Ruggedness

SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
5NM70L-AA2-R	5NM70G-AA2-R	SOT-223-2	G	D	S	Tape Reel
5NM70L-AA3-R	5NM70G-AA3-R	SOT-223	G	D	S	Tape Reel
5NM70L-TA3-T	5NM70G-TA3-T	TO-220	G	D	S	Tube
5NM70L-TF1-T	5NM70G-TF1-T	TO-220F1	G	D	S	Tube
5NM70L-TF2-T	5NM70G-TF2-T	TO-220F2	G	D	S	Tube
5NM70L-TF3-T	5NM70G-TF3-T	TO-220F	G	D	S	Tube
5NM70L-TM3-T	5NM70G-TM3-T	TO-251	G	D	S	Tube
5NM70L-TMS-T	5NM70G-TMS-T	TO-251S	G	D	S	Tube
5NM70L-TMS2-T	5NM70G-TMS2-T	TO-251S2	G	D	S	Tube
5NM70L-TMS4-T	5NM70G-TMS4-T	TO-251S4	G	D	S	Tube
5NM70L-TMN2-T	5NM70G-TMN2-T	TO-251NS2	G	D	S	Tube
5NM70L-TN3-R	5NM70G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>5NM70G-AA2-R</p> <p>(1) Packing Type (2) Package Type (3) Green Package</p>	<p>(1) T: Tube, R: Tape Reel (2) AA2: SOT-223-2, AA3: SOT-223, TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F, TM3: TO-251, TMS: TO-251S, TMS2: TO-251S2, TMS4: TO-251S4, TN3: TO-252, TMN2: TO-251NS2 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING

SOT-223-2 / SOT-223	TO-220 / TO-220F / TO-220F1 / TO-220F2 TO-251 / TO-251S / TO-251S2 / TO-251S4 TO-252 / TO-251NS2

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V_{DSS}	700	V	
Gate-Source Voltage		V_{GSS}	± 30	V	
Drain Current	Continuous	I_D	$T_C=25^\circ\text{C}$	5.4	A
			$T_C=100^\circ\text{C}$	3.4	A
	Pulsed (Note 2)		I_{DM}	20	A
Avalanche Current (Note 2)		I_{AR}	1.2	A	
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	104	mJ	
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.0	V/ns	
Power Dissipation	SOT-223-2/SOT-223	P_D	5	W	
	TO-220		108	W	
	TO-220F/TO-220F1		36	W	
	TO-220F2				
	TO-251/TO-251S		54	W	
TO-251S2/TO-251S4					
TO-251NS2/TO-252					
Junction Temperature		T_J	+150	$^\circ\text{C}$	
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L=144\text{mH}$, $I_{AS}=1.2\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 5.0\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-223-2/SOT-223	θ_{JA}	160	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F		62.5	$^\circ\text{C}/\text{W}$
	TO-220F1/TO-220F2			
	TO-251/TO-251S		110	$^\circ\text{C}/\text{W}$
	TO-251S2/TO-251S4			
TO-251NS2/TO-252				
Junction to Case	SOT-223-2/SOT-223	θ_{JC}	25	$^\circ\text{C}/\text{W}$
	TO-220		1.16	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		3.47	$^\circ\text{C}/\text{W}$
	TO-220F2			
	TO-251/TO-251S		2.3	$^\circ\text{C}/\text{W}$
TO-251S2/TO-251S4				
TO-251NS2/TO-252				

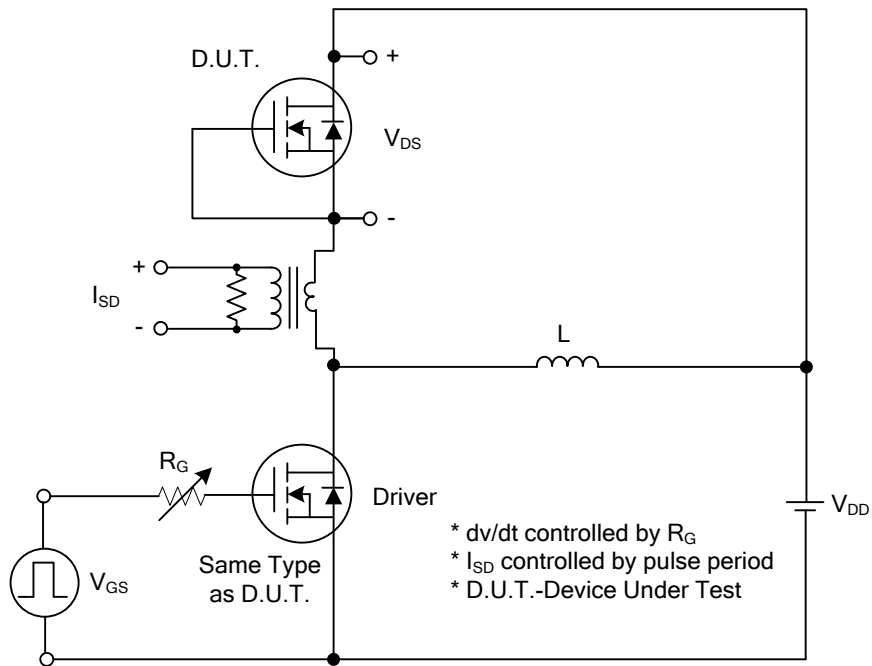
■ ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	700			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =700V, V _{GS} =0V			1	μA
Gate-Source Leakage Current	Forward	V _{GS} =30V, V _{DS} =0V			100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =2.5A			1.5	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		280		pF
Output Capacitance	C _{OSS}			135		pF
Reverse Transfer Capacitance	C _{RSS}			18		pF
Gate Resistance	R _G	V _{GS} =0V, V _{DS} =0V, f=1.0MHz		2.3		Ω
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q _G	V _{DS} =50V, V _{GS} =10V, I _D =1.3A, (Note 1, 2)		15		nC
Gate to Source Charge	Q _{GS}			5		nC
Gate to Drain Charge	Q _{GD}			4		nC
Turn-ON Delay Time (Note 1)	t _{D(ON)}	V _{DD} =30V, V _{GS} =10V, I _D =0.5A, R _G =25Ω (Note 1, 2)		5		ns
Rise Time	t _R			10		ns
Turn-OFF Delay Time	t _{D(OFF)}			50		ns
Fall-Time	t _F			60		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I _S				5	A
Maximum Body-Diode Pulsed Current	I _{SM}				20	A
Drain-Source Diode Forward Voltage (Note 1)	V _{SD}	I _S =5.0A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t _{rr}	I _S =5.0A, V _{GS} =0V, dI _F /dt=100A/μs		290		ns
Body Diode Reverse Recovery Charge	Q _{rr}				2.5	

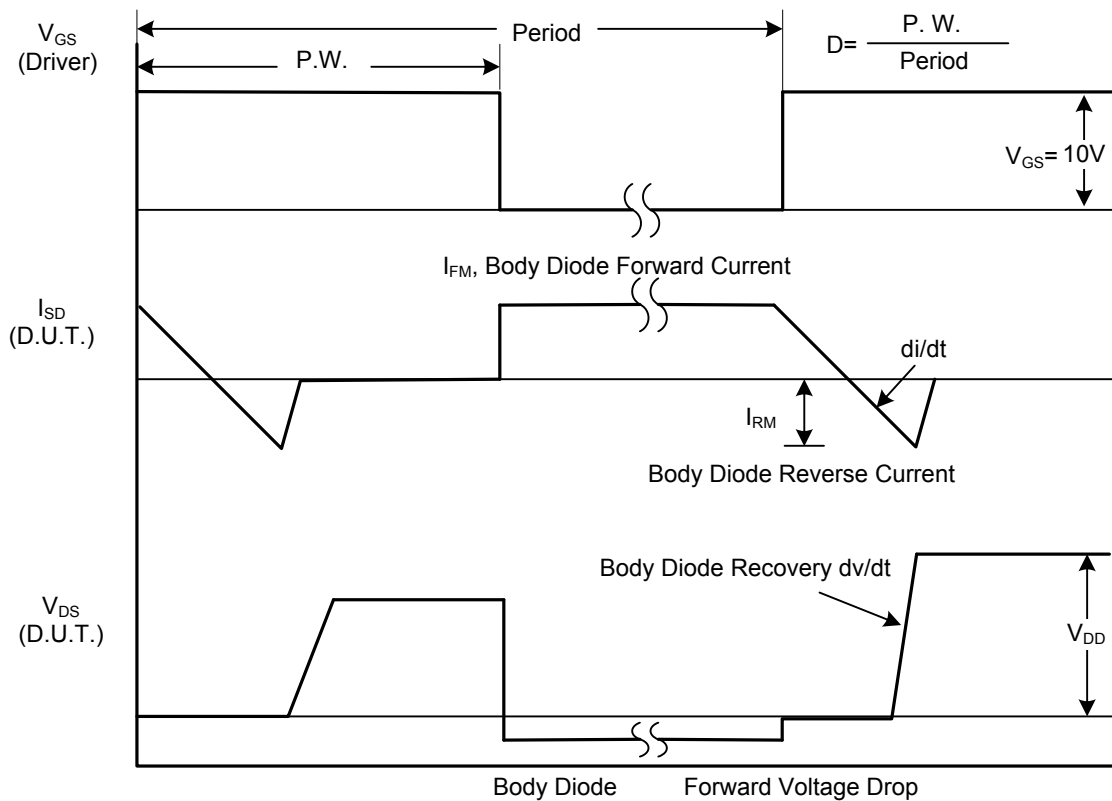
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

TEST CIRCUITS AND WAVEFORMS

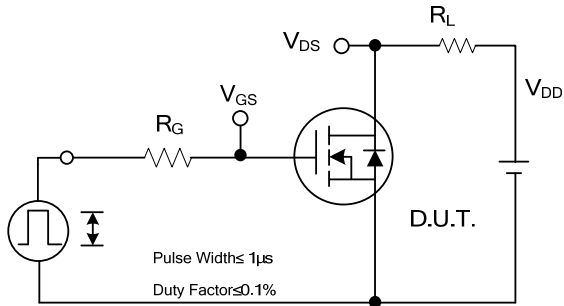


Peak Diode Recovery dv/dt Test Circuit

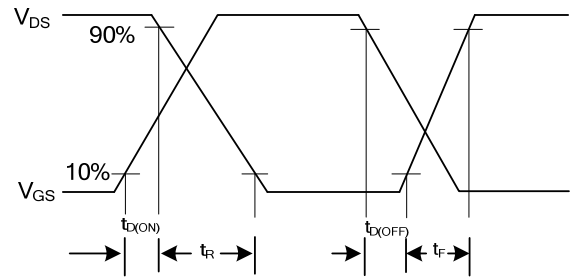


Peak Diode Recovery dv/dt Waveforms

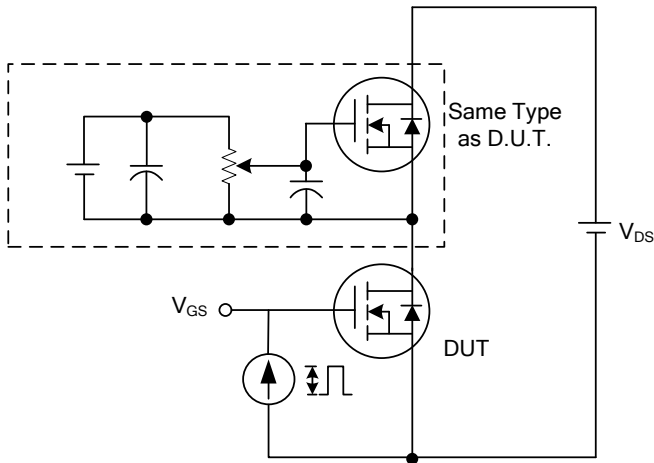
TEST CIRCUITS AND WAVEFORMS



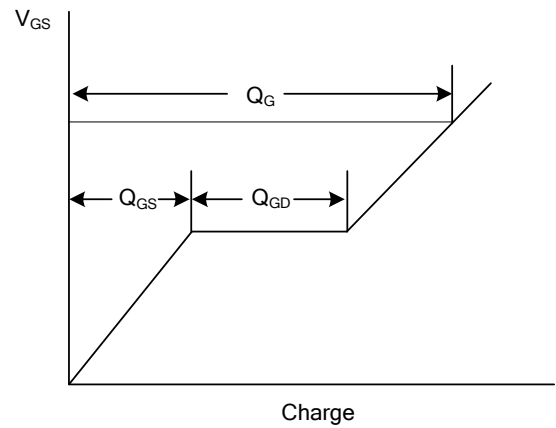
Switching Test Circuit



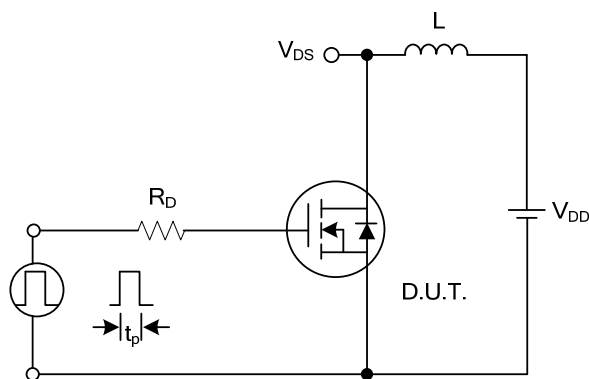
Switching Waveforms



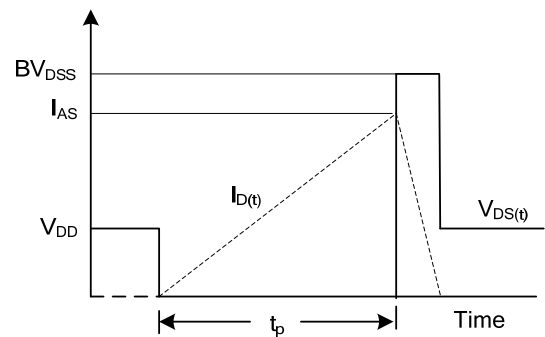
Gate Charge Test Circuit



Gate Charge Waveform

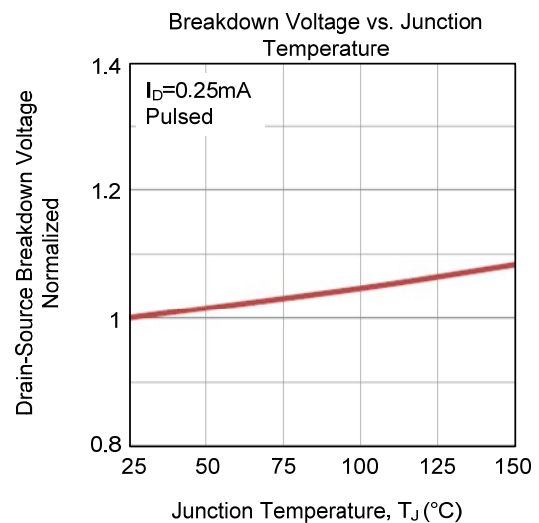
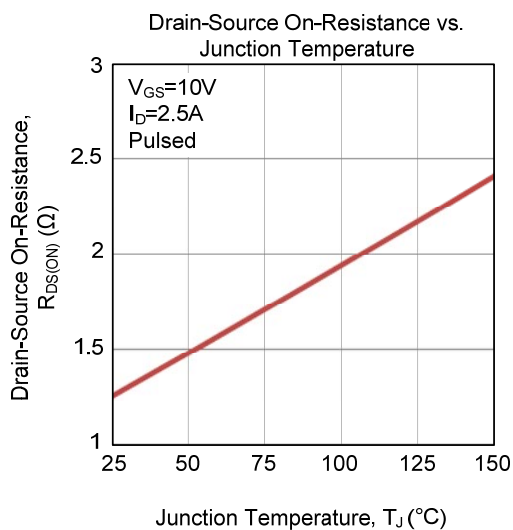
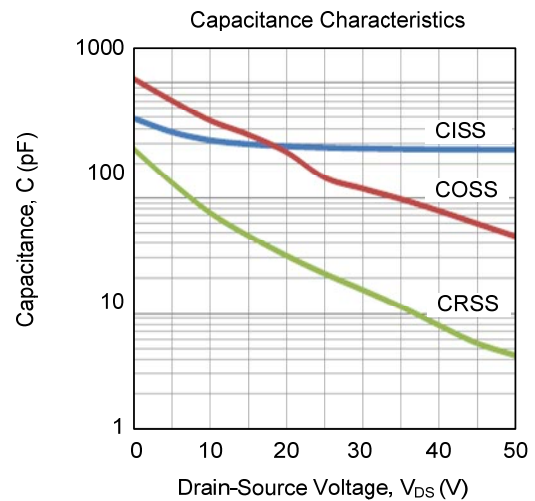
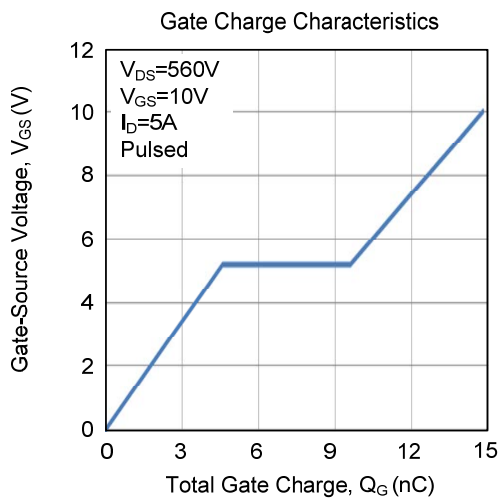
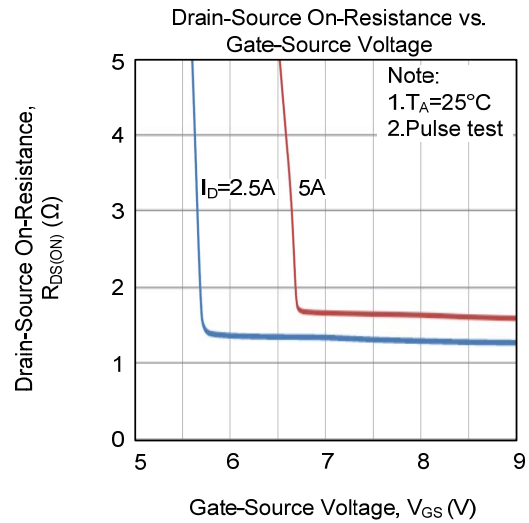
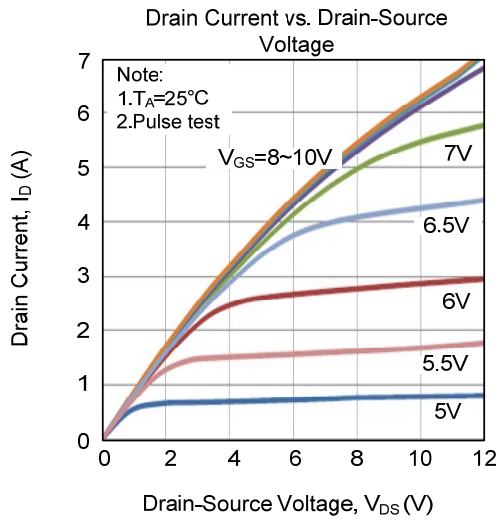


Unclamped Inductive Switching Test Circuit

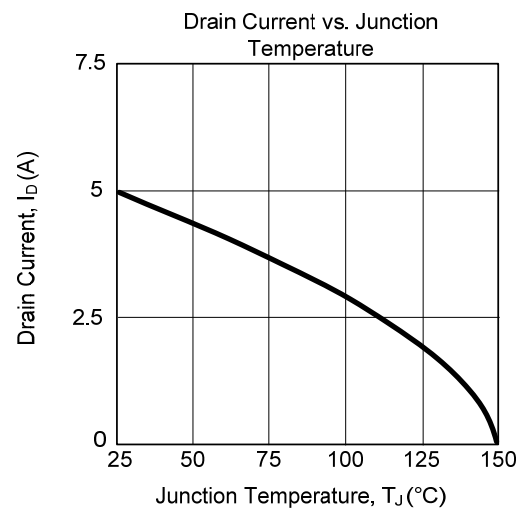
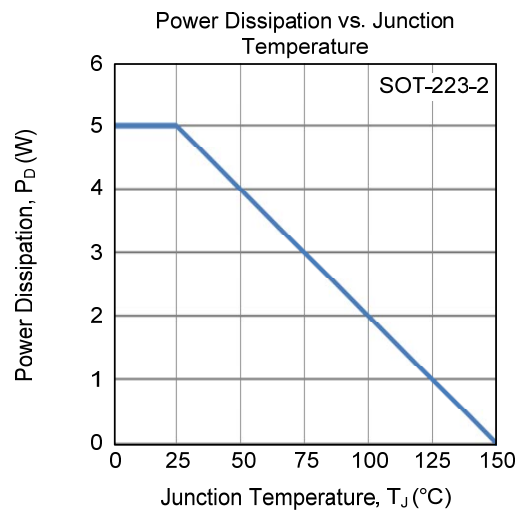
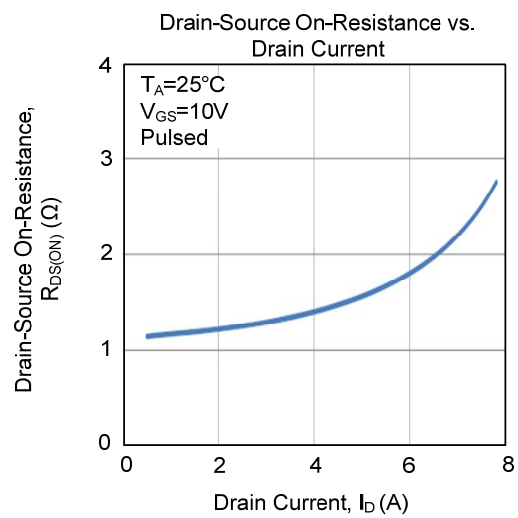
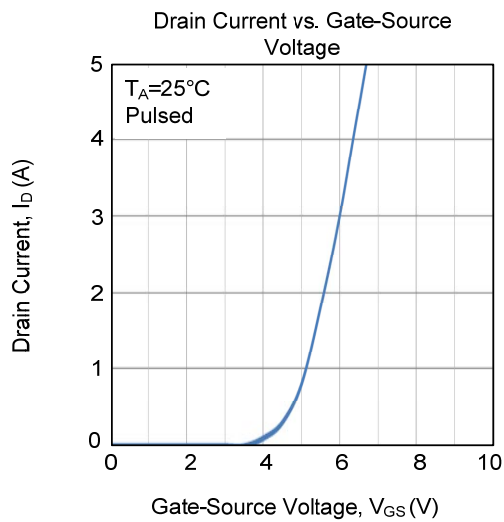
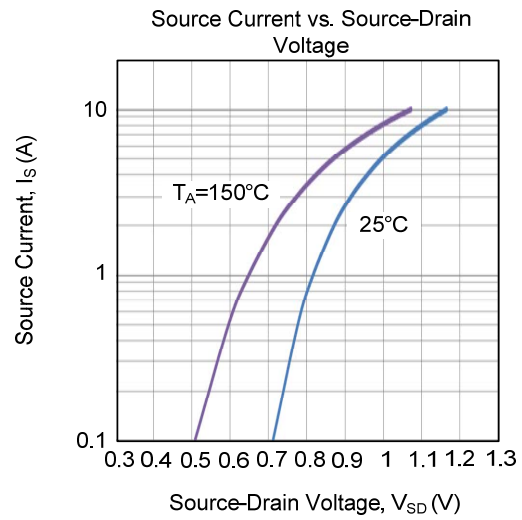
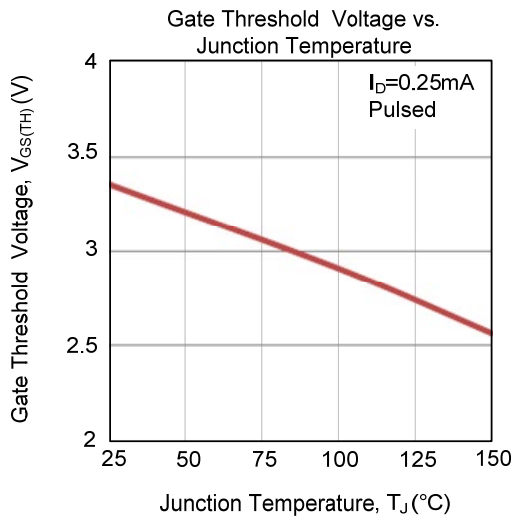


Unclamped Inductive Switching Waveforms

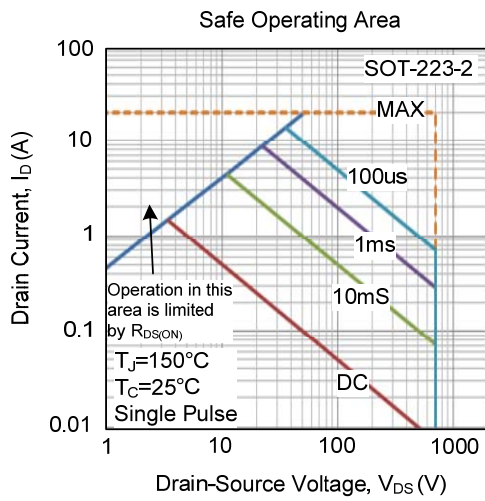
TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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